Appl. No. 10/696,463 Amdt. dated November 08, 2006 Reply to Office action of August 09, 2006

Amendments to the Specification:

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Please replace paragraph [0038] with the following amended paragraph:

[0038] Next, as shown in Fig. 3D, using deposition, photolithography, and etching, a second metal layer formed on the gate insulating layer 46 forms the pattern of data lines 34a and 34b, the source electrodes S of the TFTs 38a and 38b, and the drain electrodes D of the TFTs 38a and 38b. Preferably, the second metal layer is Cr, Ta, Ti, Al or Mo. Accordingly, the first floating BM shielding layers 42A overlap across the corresponding source electrodes S.

Please replace paragraph [0046] with the following amended paragraph:

[0046] Fig. 6 is a plane view showing a TFT-LCD device with a floating BM shielding layer functioning as a light-shielding element according to the third embodiment of the present invention. Fig. 7 is a sectional diagram along line III-III shown in Fig. 6 in order to show LC molecule orientations. The electrode array of the pixel are Ra in the third embodiment, with the similar portions omitted herein. With regard to dissimilar portions, 15 the two floating BM shielding layers have asymmetrical widths. Preferably, the first floating BM shielding layer 42A adjacent to an LC reverse region has a larger width, and

the second floating BM shielding layer 42B adjacent to an LC non-reverse region has a smaller width. Accordingly, the spacing between the data line 34a and the periphery of

the first floating BM shielding layer 42A is smaller than the spacing between the second

20 data line 34b and the periphery of the second floating BM shielding layer 42B.

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